

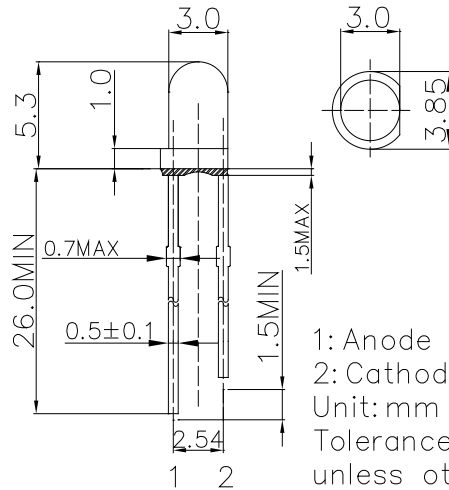
■Features

- Infrared Light Emitting Diode
- 880nm, 60mW
- Viewing angle: 30deg
- Package: 3mm clear epoxy
- UV resistant epoxy

■Applications

- IrDA
- Encoder
- Data communication
- IR camera

■Outline Dimension



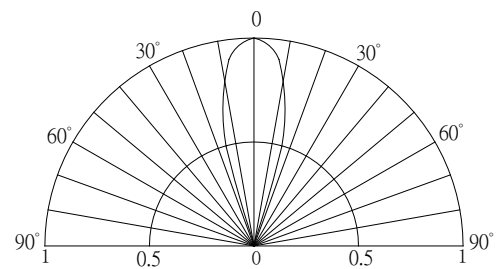
■Absolute Maximum Rating

(Ta=25°C)

Item	Symbol	Value	Unit
DC Forward Current	I_F	100	mA
Pulse Forward Current#	I_{FP}	1000	mA
Reverse Voltage	V_R	5	V
Power Dissipation	P_D	200	mW
Operating Temperature	T_{opr}	-30 ~ +85	°C
Storage Temperature	T_{stg}	-40 ~ +100	°C
Lead Soldering Temperature	T_{sol}	260°C/5sec	-

#Pulse width Max.10ms Duty ratio max 1/10

■Directivity



■Electrical -Optical Characteristics

(Ta=25°C)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
DC Forward Voltage	V_F	$I_F=100\text{mA}$	-	1.6	2.0	V
DC Reverse Current	I_R	$V_R=5\text{V}$	-	-	10	μA
Peak Wavelength	λ_p	$I_F=100\text{mA}$	866	880	892	nm
Radiant Power	P_O	$I_F=100\text{mA}$	50	60	-	mW
Radiant Intensity	I_e	$I_F=100\text{mA}$	100	150	-	mW/Sr
50% Power Angle	$2\theta_{1/2}$	$I_F=100\text{mA}$	-	30	-	deg

*1 Tolerance of measurements of Peak wavelength is $\pm 1\text{nm}$

*2 Tolerance of measurements of Radiant Intensity is $\pm 15\%$

*3 Tolerance of measurements of forward voltage is $\pm 0.1\text{V}$

GaAlAs/GaAs LED

TYPICAL ELECTRICAL/OPTICAL CHARACTERISTIC CURVES

